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Suwon-si (KR)(57) **ABSTRACT**(21) Appl. No.: **18/050,179**(22) Filed: **Oct. 27, 2022**(30) **Foreign Application Priority Data**

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A semiconductor device includes a bit line structure on a substrate, a lower contact plug on a portion of the substrate adjacent to the bit line structure, an upper contact plug including a first metal pattern on the lower contact plug and a second metal pattern contacting an upper surface and an upper sidewall of the first metal pattern, and a capacitor on the upper contact plug. The upper surface of the first metal pattern is above an upper surface of the bit line structure with respect to an upper surface of the substrate.

